

**REMARKS**

Claims 1-12 are pending in the present application. Claims 1, 2, 8, 11 and 12 have been amended herewith. Reconsideration of the claims is respectfully requested.

**I. Objection to Claims**

The Examiner objected to Claim 8, indicating that it was examined as being dependent upon Claim 7. Applicants have amended Claim 8 accordingly.

**II. 35 U.S.C. § 102, Anticipation**

The Examiner rejected Claims 1-5, 7-9 and 11-12 under 35 U.S.C. § 102 as being anticipated by Vathulya et al. (US 6,297,524). This rejection is respectfully traversed.

With respect to Claim 1, such claim has been amended to emphasize the unique physical relationships between the components comprising the semiconductor capacitor, and in particular to emphasize that the first outer and inner plates are substantially coplanar with one another, and that the second outer and inner plates are similarly substantially coplanar with one another. Per the Examiner's reading of Vathulya, the first inner plate is located on layer L4 and the first outer plate is located on layer L3, and thus the first inner plate and first outer plate of Vathulya are not substantially co-planar with one another.

Further, it is not possible to somehow reconfigure the interpretation of Vathulya's teachings to meet these newly added features and yet maintain (i) the second inner plate being located within a first hole in the first outer plate, and (ii) the first inner plate being located within a second hole in the second outer plate, as expressly recited in Claim 1. Thus, in addition to not being anticipated by the cited reference, it is submitted that amended Claim 1 is not obvious in view of the cited reference. It is also urged that due to this unique and non-obvious co-planar relationship, the claimed invention advantageously provides increased capacitive density over that of the teachings of Vathulya for a given vertical dimension.

Applicants initially traverse the rejection of dependent Claims 2-5, 7-9 and 11-12 for reasons given above with respect to amended Claim 1.

Further with respect to Claim 2, such claim has been amended to further emphasize the unique physical relationships between the components comprising the semiconductor capacitor, and in particular to emphasize that the first and second conductive sections are substantially coplanar with one another. The claimed invention per Claim 2 advantageously provides increased capacitive density over that of the teachings of Vathulya for a given vertical and lateral dimension.

Therefore, the rejection of Claims 1-5, 7-9 and 11-12 under 35 U.S.C. § 102 has been overcome.

### **III. 35 U.S.C. § 103, Obviousness**

The Examiner rejected Claims 6 and 10 under 35 U.S.C. § 103 as being unpatentable over Vathulya et al. (US 6,297,524). This rejection is respectfully traversed for similar reasons to those given above with respect to amended Claim 1 (of which Claims 6 and 10 depend upon).

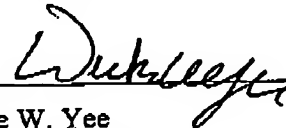
Therefore, the rejection of Claims 6 and 10 under 35 U.S.C. § 103 has been overcome.

**IV. Conclusion**

It is respectfully urged that the subject application is patentable over the cited reference and is now in condition for allowance. The Examiner is invited to call the undersigned at the below-listed telephone number if in the opinion of the Examiner such a telephone conference would expedite or aid the prosecution and examination of this application.

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Respectfully submitted,



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